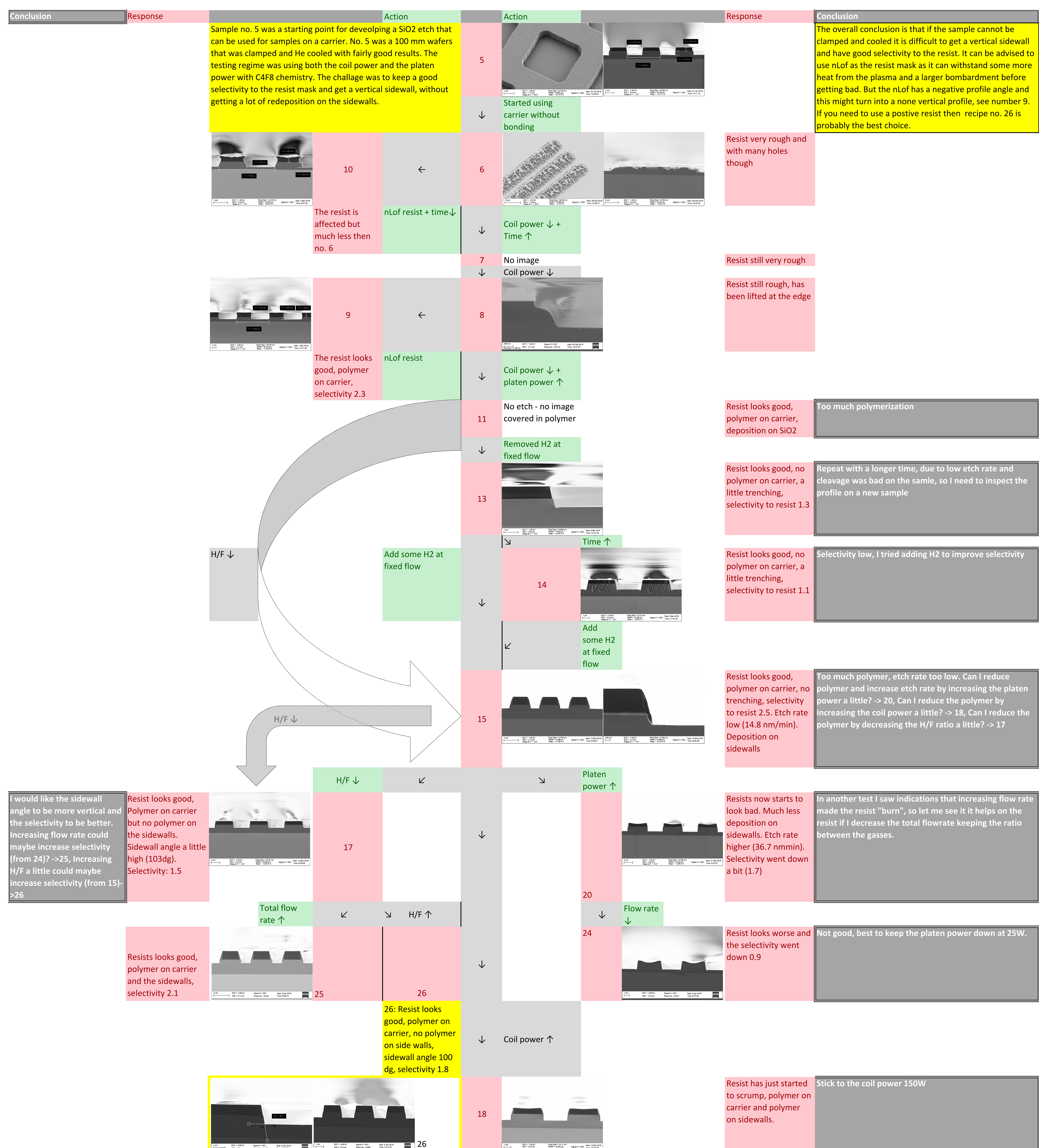

Recipe settings:	sample no.	SiO2 before etch	Resist before etch	Coil power	Platen power	Pressure	C4F8 flow	H2 flow	Process Time	Etch rate in SiO2	Etch rate in resist	Selectivity to resist (SiO2:Resist)
All temperature at 20 dg. C	**5**	1975 nm	1382 nm (mir)	800 W	15 W	2.5 mTorr	13 sccm	26 sccm	15 min	63 nm/min	27 nm/min	2.3
	6	1975 nm	1382 nm (mir)	800 W	15 W	2.5 mTorr	13 sccm	26 sccm	15 min	79 nm/min	>92 nm/min	<0.8
	7	1975 nm	1382 nm (mir)	400 W	15 W	2.5 mTorr	13 sccm	26 sccm	25 min	27 nm/min		
	8	1975 nm	1382 nm (mir)	300 W	15 W	2.5 mTorr	13 sccm	26 sccm	15 min	27 nm/min		
	9	1975 nm	1437 nm nLof	300 W	15 W	2.5 mTorr	13 sccm	26 sccm	15 min	37 nm/min	16 nm/min	2.3
	10	1975 nm	1437 nm nLof	800 W	15 W	2.5 mTorr	13 sccm	26 sccm	10 min	78 nm/min	74 nm/min	1.1
	11	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	13 sccm	26 sccm	20 min	0 nm/min		
	13	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	49 sccm	0 sccm	20 min	27.7 nm/min	20.3 nm/min	1.3
	14	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	49 sccm	0 sccm	30 min	29.9 nm/min	26.6 nm/min	1.1
	15	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	29 sccm	20 sccm	30 min	14.8 nm/min	6.0 nm/min	2.5
	17	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	39 sccm	10 sccm	30 min	26.0 nm/min	16.7 nm/min	1.5
	18	1975 nm	1382 nm (mir)	200 W	25 W	2.5 mTorr	29 sccm	20 sccm	30 min	27.6 nm/min	14.7 nm/min	1.9
	20	1975 nm	1382 nm (mir)	150 W	50 W	2.5 mTorr	29 sccm	20 sccm	30 min	36.7 nm/min	21.0 nm/min	1.7
	24	1975 nm	1382 nm (mir)	150 W	50 W	2.5 mTorr	15 sccm	10 sccm	30 min	43.5 nm/min	~46 nm/min	~0.9
	25	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	78 sccm	20 sccm	30 min	14.7 nm/min	7.1 nm/min	2.1
	26	1975 nm	1382 nm (mir)	150 W	25 W	2.5 mTorr	36 sccm	13 sccm	30 min	22.1 nm/min	12.5 nm/min	1.8